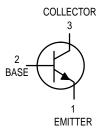
# **Switching Transistors NPN Silicon**



## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	15	Vdc
Collector-Emitter Voltage	VCES	40	Vdc
Collector-Base Voltage	VCBO	40	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	4.5	Vdc
Collector Current (10 μs pulse)	IC(Peak)	500	mA
Collector Current — Continuous	IC	200	mA
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	0.36 2.06	Watt mW/°C
Total Device Dissipation @ T <sub>C</sub> = 100°C Derate above 100°C	PD	0.68 6.85	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>Stg</sub>	-65 to +200	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	486	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	147	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 μA, V <sub>BE</sub> = 0)		V(BR)CES	40	_	Vdc
Collector-Emitter Sustaining Voltage <sup>(1)</sup> (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)		VCEO(sus)	15	_	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>B</sub> = 0)		V(BR)CBO	40	_	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		V(BR)EBO	4.5	_	Vdc
Collector Cutoff Current ( $V_{CB} = 20 \text{ Vdc}$ , $I_{E} = 0$ ) ( $V_{CB} = 20 \text{ Vdc}$ , $I_{E} = 0$ , $T_{A} = 150^{\circ}\text{C}$ )	2N2369 2N2369A	ICBO	_ _	0.4 30	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 20 Vdc, V <sub>BE</sub> = 0)	2N2369A	ICES	_	0.4	μAdc
Base Current (V <sub>CE</sub> = 20 Vdc, V <sub>BE</sub> = 0)	2N2369A	IB	_	0.4	μAdc

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

Preferred devices are Motorola recommended choices for future use and best overall value.



\*Motorola Preferred Device



CASE 22-03, STYLE 1 TO-18 (TO-206AA)



## 2N2369 2N2369A

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain(1) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 1.0 Vdc)	2N2369 2N2369A	hFE	40 —	120 120	_
$(I_C = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}, T_A = -55^{\circ}C)$	2N2369		20	_	
(I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = $0.35$ Vdc, T <sub>A</sub> = $-55^{\circ}$ C) (I <sub>C</sub> = 30 mAdc, V <sub>CE</sub> = $0.4$ Vdc)	2N2369A 2N2369A		20 30	_	
$(I_C = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N2369A		20	_	
$(I_C = 100 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc})$	2N2369		20	_	
Collector-Emitter Saturation Voltage <sup>(1)</sup> (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)	2N2369 2N2369A	VCE(sat)		0.25 0.20	Vdc
$(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}, T_A = +125^{\circ}C)$ $(I_C = 30 \text{ mAdc}, I_B = 3.0 \text{ mAdc})$	2N2369A 2N2369A			0.30 0.25	
$(I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc})$	2N2369A		_	0.50	
Base-Emitter Saturation Voltage(1) (IC = 10 mAdc, IB = 1.0 mAdc) (IC = 10 mAdc, IB = 1.0 mAdc, $T_A = +125^{\circ}C$ ) (IC = 10 mAdc, IB = 1.0 mAdc, $T_A = -55^{\circ}C$ ) (IC = 30 mAdc, IB = 3.0 mAdc)	All Types 2N2369A 2N2369A 2N2369A	VBE(sat)	0.70 0.59 —	0.85 — 1.02 1.15	Vdc
$(I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc})$	2N2369A		_	1.60	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 10 Vdc, f = 100 MHz)		fΤ	500	_	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	_	4.0	pF
Input Capacitance (VEB = 1.0 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ibo</sub>	_	4.0	pF
SWITCHING CHARACTERISTICS					
Storage Time ( $I_C = I_{B1} = 10 \text{ mAdc}$ , $I_{B2} = -10 \text{ mAdc}$ )		t <sub>S</sub>	_	13	ns
Turn–On Time (I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 3.0 mA, I <sub>B2</sub> = $-1.5$ mA, V <sub>CC</sub> = 3.0 Vdc	c)	<sup>t</sup> on	_	12	ns
Turn–Off Time (I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 3.0 mA, I <sub>B2</sub> = $-1.5$ mA, V <sub>CC</sub> = 3.0 Vdc	c)	t <sub>off</sub>	_	18	ns

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

# SWITCHING TIME EQUIVALENT TEST CIRCUITS FOR 2N2369, 2N3227

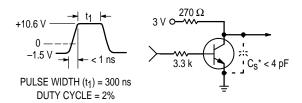


Figure 1. ton Circuit — 10 mA

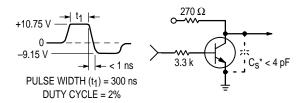


Figure 3. toff Circuit — 10 mA

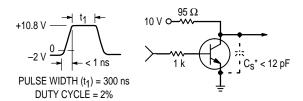


Figure 2. ton Circuit — 100 mA

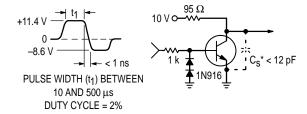


Figure 4. toff Circuit — 100 mA

<sup>\*</sup> Total shunt capacitance of test jig and connectors.

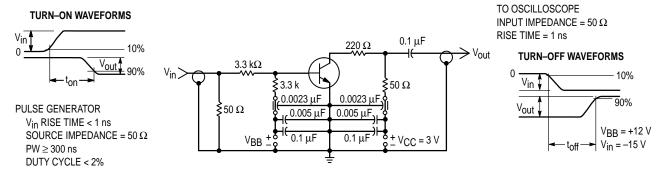
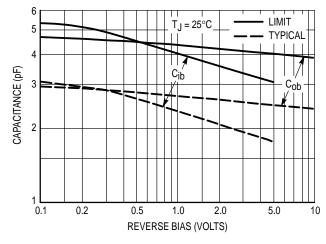


Figure 5. Turn-On and Turn-Off Time Test Circuit



**Figure 6. Junction Capacitance Variations** 

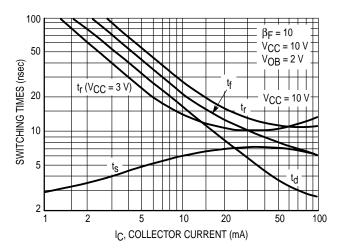


Figure 7. Typical Switching Times

## 2N2369 2N2369A

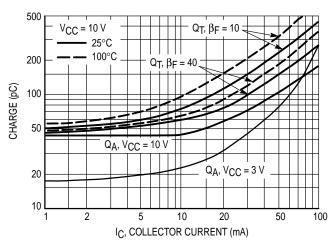


Figure 8. Maximum Charge Data

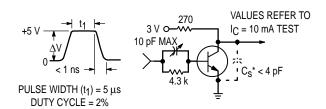


Figure 9. Q<sub>T</sub> Test Circuit

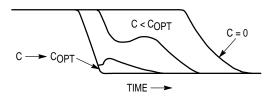


Figure 10. Turn-Off Waveform

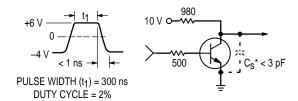


Figure 11. Storage Time Equivalent Test Circuit

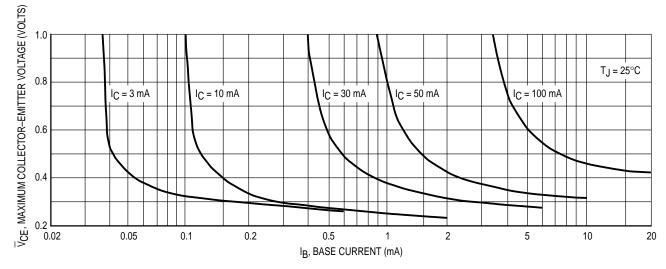
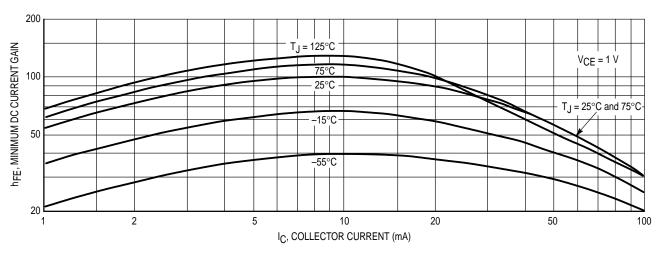


Figure 12. Maximum Collector Saturation Voltage Characteristics



**Figure 13. Minimum Current Gain Characteristics** 

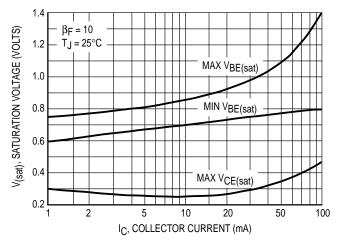
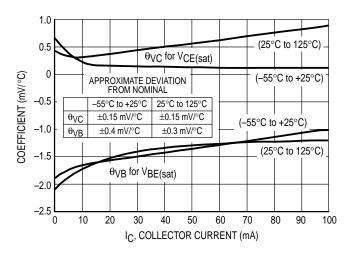
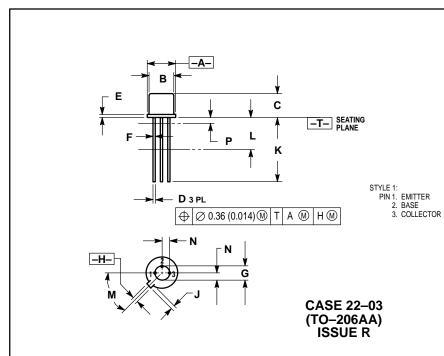


Figure 14. Saturation Voltage Limits



**Figure 15. Typical Temperature Coefficients** 

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- CONTROLLING DIMENSION: INCH.
  DIMENSION J MEASURED FROM DIMENSION A
- DIMENSION F APPLIES BETWEEN DIMENSION P AND L. DIMENSION D APPLIES BETWEEN DIMENSION L AND K MINIMUM. LEAD DIAMETER IS UNCONTROLLED IN DIMENSION P AND
- BEYOND DIMENSION K MINIMUM.
  5. DIMENSION E INCLUDES THE TAB THICKNESS. (TAB THICKNESS IS 0.51(0.002) MAXIMUM).

•			. ,	,
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.209	0.230	5.31	5.84
В	0.178	0.195	4.52	4.95
С	0.170	0.210	4.32	5.33
D	0.016	0.021	0.406	0.533
Е		0.030		0.762
F	0.016	0.019	0.406	0.483
G	0.100	0.100 BSC		BSC
Н	0.036	0.046	0.914	1.17
J	0.028	0.048	0.711	1.22
K	0.500		12.70	
L	0.250		6.35	
M	45 °BSC		45°	BSC
N	0.050	BSC	1.27	BSC
Р		0.050		1 27

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